

Title (en)
MEMORY CELL

Title (de)
SPEICHERZELLE

Title (fr)
CELLULE DE MEMOIRE

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Application
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Abstract (en)
[origin: WO03017374A2] The invention relates to a memory cell comprising a source region, a drain region, a control gate which is situated on the source side, a control gate which is situated on the drain side, an injection gate which is arranged between the source-side control gate and the drain-side control gate, a source-side memory element which is arranged in relation to the source-side control gate, and a drain-side memory element which is arranged in relation to the drain-side control gate. In order to program the memory cell, a low electrical voltage is applied to the injection gate and a high electrical voltage is applied to the control gate.

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